

Patent Claims

1. Method to produce electronic components with closely adjacent electrodes on a substrate characterized in that the structuring of the electrodes is achieved using the following steps:
 - a) a photo lacquer is structured on the substrate with overlapping edges;
 - b) a metal vapor is deposited onto the substrate and the structured photo lacquer;
 - c) an insulator is applied over the surface thus produced;
 - d) the insulator is etched, whereby flat edges are formed on the overlapping edges of the photo lacquer as an inverse of the overlaps.
2. Method to produce electronic components with closely adjacent electrodes on a substrate characterized in that the structuring of the electrodes is achieved using the following steps:
 - a) a metal layer is deposited onto the substrate;
 - b) a photo lacquer is structured on the metal layer;
 - c) the exposed metal layer is etched, whereby overhangs arise in the photo lacquer by means of controlled undercutting of the metal;
 - d) The surface thus produced is exposed to metal vapor;
 - e) the photo lacquer with its metal layer is removed.
3. Method to produce electronic components with closely adjacent electrodes on a transparent substrate characterized in that:
 - a) The electrodes are structured on the substrate as in Claim 2;
 - b) A transparent organic semi-conductor and a transparent insulator are deposited on the surface,
 - c) A second photo lacquer is deposited on the upper side, and photo lithography is performed on the underside,
 - d) a metal vapor is deposited onto the surface thus produced,
 - e) the remaining photo lacquer with its metal layer is removed,
 - f) the electronic component is completed by etching the contacts until they are exposed.
4. Method to produce electronic components with closely adjacent electrodes on a substrate characterized in that:
 - a) The electrodes are structured on the substrate as in Claim 2;

- b) Holes or grooves are etched into the substrate at those positions without metal,
- c) A second thin metal layer is deposited,
- d) An insulator is applied,
- e) The insulator on the upper side of the substrate is etched;
- f) An organic semi-conductor is applied and the surface is sealed,
- g) The buried gates are exposed using a photolithographic process.